

Table of Contents

Preface.....	iii
State-Of-The-Art Program on Compound Semiconductors XLI	
Recent Progress on InP HBT Technology and Applications*	1
<i>A. Gutierrez-Aitken, D. Sawdai, P. Chang, C. Monier, V. Gambin, A. Cavus, M. Barsky, B. Oyama, J. Matsui, K. Tsai, B. Chan and A. K. Oki</i>	
Characterization of InGaAs Self-Mixing Detectors for Amplitude-Modulated LADAR (CAML)*	12
<i>M. Gerhold, K. Aliberti, H. Shen, P. R. Mehandru, S. Jang, S. Pearton and F. Ren</i>	
Advanced GaAs HEMT Technologies for Ultra Low-Noise and Millimeter Wave Power Applications*	24
<i>M.-Y. Kao, M. S. Heins, S. Chen, Q. Wang, J. Delaney, S. Nayak, E. A. Beam III, and P. Saunier</i>	
Unique Capabilities of Chemically-Assisted Ion-Beam Etching for Compound Semiconductor Devices*	35
<i>G. A. Vawter and C. Alford</i>	
An Innovative Planarization Technology For Ultra High Frequency InP/InGaAs Heterojunction Bipolar Transistor (HBT) Manufacturing*	44
<i>X. Zeng P.C. Chang, J. Yamamoto, D. Sawdai, A. Gutierrez-Aitken, M. Barsky, S. Olson, and A. Oki</i>	
Spectrometric Monitoring Method for Concentration of Hydrogen Peroxide in Chemical Etching Solution of GaAs	51
<i>K. Shigyo, S. Umemura, and M. Kinugaw</i>	
Effects of Nano-sized Interface on the Electrical Resistances of the P-GaAs Wafer Bonding	60
<i>H. Ouyang, J.-H. Cheng, and Y.-C. S. W</i>	
Characterization of 1.55 μ m Light Emitting β -FeSi ₂ Nano-dots and Metallic Silicide Nano-wires*	65
<i>L.-J. Chou, Y.-L. Cheuh, S.-L. Cheng, H.-F. Ho, and M.-T. Chang</i>	

MgZnO/ZnO Heterostructures for UV Light Emitters and Spintronic Applications: Material Growth and Device Design <i>A. Osinski, J. W. Dong, M. Z. Kauser, B. Hertog, A. M. Dabiran, C. Plaut, P. P. Chow, S. J. Pearton, X. Y. Dong, C. J. Palmstrom</i>	70
Structural and Optical Characterization of Non-polar A-plane III Nitride Thin Films Grown on R-plane ...* <i>D. Lu, A. Parekh, V. Merai, J. C. Ramer, E. S. Udovich, D. S. Lee, D. I. Florescu, M. J. Begarney, and E. A. Armou</i>	80
Numerical Simulation of the Anode Formation of Nanoporous Indium Phosphide <i>R. Lynch, C. O'Dwyer, I. Clancy, D. Corcoran, and D. N. Buckley</i>	85
Effects of Mesa Etching Processes on GaInP/GaAs Triple Barrier Resonant Tunneling Diodes* <i>M. Suhara, N. Asaoka, M. Fukumitsu, H. Horie, and T. Okumur</i>	96
Formation of Nanoporous InP by Electrochemical Anodization <i>D.N. Buckley, C. O'Dwyer, R. Lynch, D. Sutton, and S.B. Newcomb</i>	103
High Performance Planar Sub-Micron InP Heterojunction Bipolar Transistor* <i>V. Gambin, P. C. Chang, D. Sawdai, A. Cavus, X. Zeng, J. Yamamoto, K. Loi, G. S. Leslie, D. Li, J. Wang, R. Elmadjian, P. Nam, C. Grossman, M. Barsky, A. Gutierrez-Aitken, and A. Ok</i>	118
Fabrication of Indium-doped n-Fe ₂ O ₃ Thin Films by Spray Pyrolytic Deposition Method for Photoelectrochemical Water Splitting <i>W. B. Ingler Jr. and S. U. M. Kha</i>	124
III-V Ternary Bulk Crystal Growth Technology <i>P.S. Dutta</i>	134
Preparation of Cubic Silicon Carbide with Smooth Surface on Carbonized Porous Silicon <i>J. Komiyama, Y. Abe, S. Suzuki, and H. Nakanishi</i>	142
Wafer Level and Chip Size Direct Wafer Bonding at Room Temperature <i>M. M. M. Howlader and T. Suga</i>	150
Efficient Photoelectrochemical Production of Hydrogen from Water by a Carbon Modified n-TiO ₂ Thin Film Electrode <i>Y. A. Shaban and S. U. M. Khan</i>	161

Au/In ₂ Bonding of InP-Based MOEMS <i>M. Strassner, J. Dion, and I. Sagne</i>	172
High Output Power GaAs-based Vertical External Cavity Surface Emitting Lasers Achieved by AuIn ₂ Solid Liquid Inter Diffusion Bonding <i>J. Dion, I. Sagnes, M. Strassner, M. Jacquemet, P. Georges, and A. Garnache</i>	177
 Nitride and Wide Bandgap Semiconductors for Sensors, Photonics, and Electronics V	
Growth, Characterization, and Application of High Power III-Nitride Ultraviolet Emitters <i>J. Han, S.-R. Jeon, M. Gherasimova, Y.-K. Song, A.V. Nurmikko, L. Zhou, W. Goetz, and M. Krame</i>	183
Growth of Group III Nitrides on Various Plane Substrates* <i>H. Amano, A. Honshio, T. Kitano, Y. Miyake, K. Iida, T. Kawashima, M. Imura, K. Balakrishnan, M. Iwaya, S. Kamiyama and I. Akasaki</i>	192
Ultra High Output Power 365nm Ultraviolet Light Emitting Diodes <i>D. Morita, M. Yamamoto, K. Akaishi, K. Matoba, K. Yasutomo, Y. Kasai, M. Sano, S. Nagahama and T. Muka</i>	200
Rare Earth-Doped III-N Light Emitting Diodes* <i>J.M. Zavada, K.H. Kim, J.Y. Lin, H.X. Jiang, P. Chow and B. Hertog</i>	205
Plasma-Assisted MBE Growth of GaN on GaN/Sapphire Templates Grown <i>In Situ</i> by Ammonia- MBE <i>H. Tang, S. Rolfe, M. Beaulieu, I. Sproule, S. Haffouz, and J. Web</i>	215
Photoluminescence and Time-Resolved Luminescence of Quaternary InAlGaN Alloys <i>K. Fukui, S. Naoe, K. Kimura, S. Hamada and H. Hirayama</i>	225

Highly Reflective and Low Resistance Indium Oxide/Ag Ohmic Contacts to p-GaN for Flip-Chip Light Emitting Diodes <i>J.-O. Song, S.-K. Kim, D.-S. Leem, J.S. Kwak, Y. Park, and T.-Y. Seon</i>	236
Self-Organized InGaN/GaN Multiple Quantum Well Nanocolumn Light Emitting Diodes Grown on (111) Si Substrate <i>A. Kikuchi, M. Kawai, M. Tada and K. Kishin</i>	245
Si-Doped In _{0.23} Ga _{0.77} N/GaN Short-period Superlattice Tunneling Contact Layer Used on InGaN/GaN Laser Diode <i>C.J. Tun, R.C. Tu, J.K. Sheu, C.C. Chou, T.C. Wang, C.E. Tsai, and G.C. Chi</i>	254
Characterization of GaN Schottky Barrier Photodiodes With a Low-temperature GaN Cap Layer <i>M.L. Lee, J.K. Sheu, Y.K. Su, S.J. Chang, W.C. Lai, and G.C. Chi</i>	260
Fabrication of Group III-Nitride Waveguides by Inductively Coupled Plasma Etching <i>N. Li, I. Waki, C. Kumtornkittikul, J.-H. Liang, M. Sugiyama, Y. Shimogaki, and Y. Nakano</i>	270
Charge and Spin-Based Electronics Using ZnO Thin Films <i>D.P. Norton, Y.W. Heo, M. Ivill, Y. Li, Y.W. Kwon, J. M. Erie, M. Jones, P.H. Holloway, S. J. Pearton, F. Ren, Z.V. Park, S. Li, A. F. Hebard and J.Kelly</i>	276
Sensors Based on SiC-AlN MEMS* <i>D. Doppalapudi, R. Mlcak, J. Chan, H. L. Tuller, J. Abell, W. Li and T.D. Moustaka</i>	287
Anomalous Hall Effect in Wide Bandgap Diluted Magnetic Semiconductors Co-Doped With Non-Magnetic Impurities <i>Y.D. Park, H.K. Choi, S.B. Shim, K.S. Suh, S.S.A. Seo, T.W. Noh, Y.S Kim, J.S. Lee, Z.G. Khim, C.R. Abernathy, S.J. Pearton, J.M. Zavada</i>	300
Effective Nitrogen Doping of Zinc Oxide <i>S. Lee, Y. Yan, S. Yoon, C. Perkins, E. Tracy, and J.R. Pitts</i>	312
Spin-Polarization of Excitons in GaN <i>A. Tackeuchi, T. Kuroda, K. Taniguchi, T. Chinone and N. Horio</i>	320
Biexcitons in GaN and AlGaN Epitaxial Layers* <i>Y. Yamada</i>	326

Study of Long Time-Scale Photoluminescence Dynamics of GaN/InGaN Quantum Wells and Comparison With Samples Grown on ELOG-GaN <i>R. Micheletto, M. Abiko, A. Kaneta, Y. Narukawa, T. Mukai and Y. Kawakami</i>	341
Enhanced Light Extraction and Spontaneous Emission From Textured GaN Templates Formed During Growth by the HVPE Method <i>J.S. Cabalu, C. Thomidis, T.D. Moustakas and S. Riyopoulo</i>	351
Electrical Properties for InN Grown by Molecular Beam Epitaxy <i>W.J. Schaff, H. Lu, L. F. Eastman, W. Walukiewicz, K. Man Yu, S. Keller, S. Kurtz, B. Keyes, L. Gevila</i>	358
Self-Assembled Indium Nitride Nanocolumns Grown by Molecular Beam Epitaxy <i>H.M. Ng, R. Liu and F.A. Ponc</i>	372
Carrier Trapping and Thermal Effects in GaN-based High-electron Mobility Transistors <i>A.M. Dabiran, A. Osinsky, P.P. Chow, Z. Zhang, A. Madjar, S. Osinsky, J.C.M. Hwang, R.C. Fitch, J. Gillespie, G. Jessen, N. Moser, and A. Crespo</i>	380
High Voltage AlGaIn/GaN Power HEMT for Power Electronics Applications <i>I. Omura, W. Saito and K. Tsuda</i>	386
Recent Development of Nitride Heterojunction Bipolar Transistors <i>T. Makimoto and K. Kumakura</i>	395
Material, Process, and Device Development of GaN-Based HFETs on Silicon Substrates <i>J.W. Johnson, J. Gao, K. Lucht, J. Williamson, C. Strautin, J. Riddle, R. Therrien, P. Rajagopal, J.C. Roberts, A. Vescan, J.D. Brown, A. Hanson, S. Singhal, R. Borges, E.L. Piner, and K.J. Linthicum</i>	405
Insulated Gate and Surface Passivation Structures for GaN-Based FETs <i>T. Hashizume and H. Hasegaw</i>	420
Pulse Testing of AlGaIn/GaN HEMT <i>A.G. Baca, Y.M. Kim, P.F. Marsh, M.G. Armendariz, C.E. Sandoval, A.A. Allerman, S.R. Kurtz, M.E. Overberg, J.R. Wendt, and C.A. Sanche</i>	435
4H-SiC Planar MESFETs With f_{\max} of 40 GHz Without Trapping Effect <i>H.J. Na, S.Y. Jung, J.H. Yim, M.Y. Um, H.K. Song, and H.J. Kim</i>	441

High-Voltage and High-Frequency Operation of AlGa _N /Ga _N Power Heterojunction FET <i>H. Miyamoto, Y. Ando, Y. Okamoto, T. Nakayama, K. Hataya, T. Inoue, M. Senda, K. Hirata, M. Kosaki, N. Shibata and M. Kuzuhara</i>	446
High performance Ga _N HEMTs for mmWave Applications <i>K.S. Boutros, M. Regan, P. Rowell, and B. Bra</i>	454
Effect of Silicon Nitride PECVD Growth on AlGa _N /Ga _N HEMT Dispersion and Breakdown Characteristics <i>R. Fitch, J. Gillespie, D. Via, D. Agresta, T. Jenkins, G. Jessen, N. Moser, A. Crespo, A. Dabiran, A. Osinsk</i>	459
High Breakdown Field (> 15MV/cm) on Crystalline β-Ga ₂ O ₃ /Ga _N Metal Oxide Semiconductor Devices <i>L.-H. Peng, and H.-M. Wu</i>	465
Low-dislocation-density Ga _N and AlGa _N Using Epitaxial-lateral-overgrowth Methods <i>K. Hiramatsu and H. Miyak</i>	472
Molecular Beam Epitaxy of Ga _N on Lattice-Matched Zirconium Diboride Substrates Using Low-Temperature Ga _N and Al _N Nucleation Layers <i>R. Armitage, J. Suda, and T. Kimoto</i>	484
Self-Oriented Growth of Ga _N Films on Molten Gallium <i>H. Li, H. Chandrasekaran, M.K. Sunkara, M. Stukowski, and K. Rajan</i>	496
Simulation Study for RF-MBE of Ga _N (0001) Using the First Principles Calculation and the Kinetic Monte Carlo Method <i>A. Ishii, M. Taniguchi, K. Fujiwara and S. Koyam</i>	504
Studies of Electron Trapping in III-Nitrides <i>L. Chernyak, W. Burdett, O. Lopatiuk, and M. Eickhoff</i>	512
Planar Ga _N -Based UV Photodetectors Formed by Si Implantation <i>M.C. Chen, J.K. Sheu, M.L. Lee, C.J. Kao, C.J. Tun, and G.C. Ch</i>	522
Direction of Excited Carriers from Low in a Facet on InGa _N Microcrystals Observed in the Highly Spatially Resolved Cathodoluminescent Images <i>H. Kanie and S. Kobayashi</i>	529

Advances in Characterization of III-Nitrides by Secondary Ion Mass Spectrometry <i>P.V. Lierde, C. Tian, R.A. Hockett, L. Wei, D.S. Hockett, P.C. Alejandro, S. Keller, and S.P. DenBaars</i>	535
TEM Characterization of MBE-Grown Core/Shell (Zn,Mg)O Nanowires <i>K. Pruessner, Y.-W. Heo, M.J. Kaufman, M.F. Chisholm, and D. P. Norton</i>	540
Photoelectrochemical Investigation of the Etching of GaN in H ₃ PO ₄ <i>C. Heffernan, D.N. Buckley, and C. O’Raifeartaig</i>	552
Control of Surface Morphology in Photoelectrochemical Etching of GaN <i>B. Yang and P. Fay</i>	564
Enhancement of Ionization Efficiency of Acceptors by Their Excited States in Heavily Doped p-Type GaN and Wide Bandgap Semiconductors <i>H. Matsuura</i>	570
Homoepitaxial Growth of Iron-Doped 4H-SiC by Bis-Trimethylsilylmethane and Ferrocene Precursors for Semi-Insulating Si <i>H. K. Song, J. K. Jeong, S. G. Kim, M. Y. Um, H. J. Na, S. Y. Jung, H. S. Seo, J. H. Yim, J. B. Lee, and H. J. Kim</i>	582
Single Crystal Growth of Gallium Nitride by Slow-Cooling of Its Congruent Melt Under High Pressure <i>H. Saitoh, W. Utsumi, H. Kaneko, K. Kiriya, and K. Aoki</i>	587
Author Index	595
Subject Index	599